



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03A Plastic-Encapsulate Diode

DAN222E

SWITCHING DIODE

DESCRIPTION

Epitaxial planar Silicon diode

FEATURES:

High speed. (trr=1.5ns Typ.)

Suitable for high packing density layout

High reliability.

APPLICATION

Ultra high speed switching

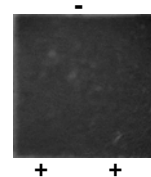
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

WBFBP-03A

(1.6×1.6×0.5)

unit: mm

TOP



1. ANODE

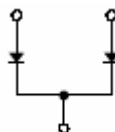
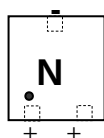
2. ANODE

3.CATHODE

BACK



MARKING: N



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25 °C

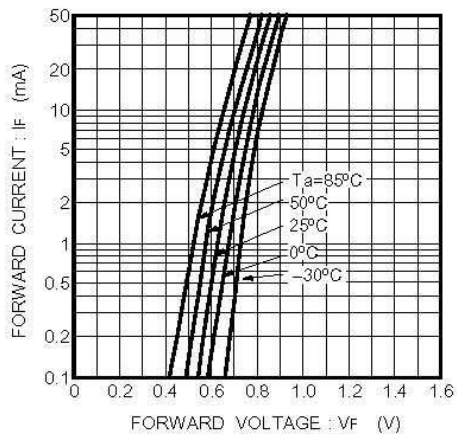
Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	80	V
DC reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300	mA
Average forward current	I _O	100	mA
Power dissipation	P _D	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

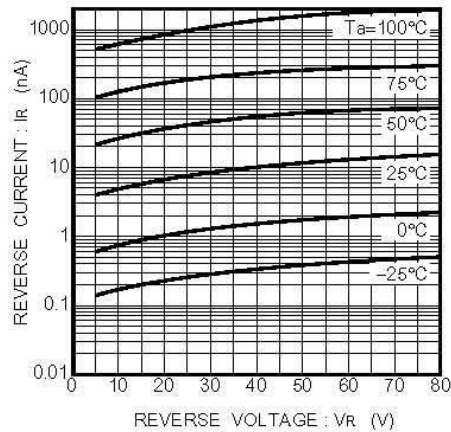
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 100μA	80		V
Reverse voltage leakage current	I _R	V _R =70V		0.1	μA
Forward voltage	V _F	I _F =100mA		1.2	V
Diode capacitance	C _D	V _R =6V, f=1MHz		3.5	pF
Reverse recovery time	t _{rr}	V _R =6V, I _F =5mA		4	ns

Typical Characteristics

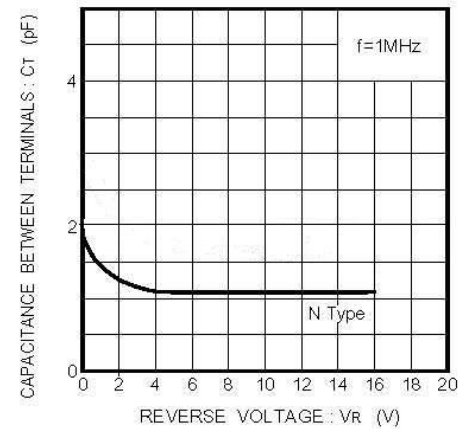
DAN222E



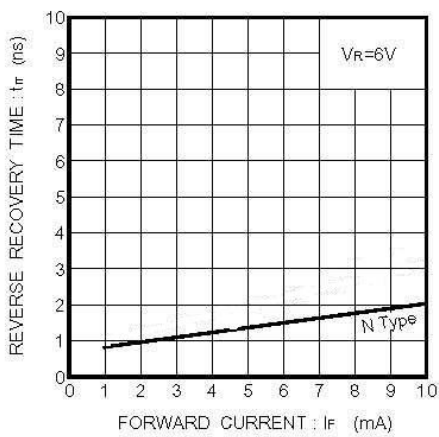
Forward characteristics



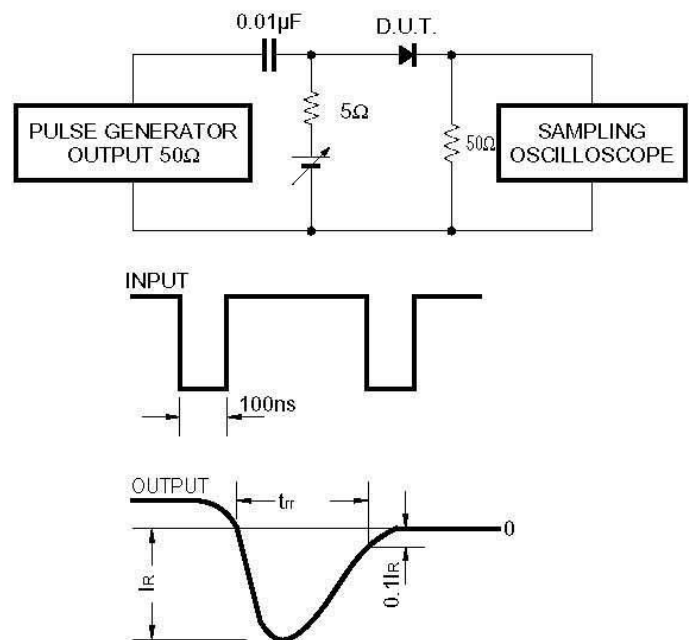
Reverse characteristics



Capacitance between terminals characteristics



Reverse recovery time



Reverse recovery time (t_r) measurement circuit

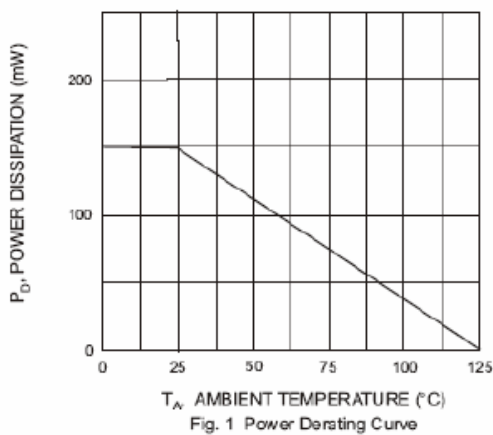


Fig. 1 Power Derating Curve